Sanghoon Lee

List of Publications by Year
in descending order

117 papers	1,067 citations	567281 15 h-index	501196 28 g-index
118 all docs	118 docs citations	118 times ranked	706 citing authors

#	Article	IF	Citations
1	Gate control of interlayer exchange coupling in ferromagnetic semiconductor trilayers with perpendicular magnetic anisotropy. APL Materials, 2022, 10, 041102.	5.1	0
2	Controllable Exchange Bias Effect in (Ga, Mn)As/(Ga, Mn)(As, P) Bilayers With Non-Collinear Magnetic Anisotropy. IEEE Transactions on Magnetics, 2021, 57, 1-4.	2.1	2
3	Quantitative determination of spinâ€“orbit-induced magnetic field in GaMnAs by field-scan planar Hall measurements. Scientific Reports, 2021, 11, 10263.	3.3	6
4	Magnetic anisotropy of ferromagnetic <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Ga</mml:mi><mml:mrow><mml:mn>1</mm mathvariant="normal">P</mml:mi><mml:mi>y</mml:mi></mml:msub></mml:mrow></mml:math> films with graded. Physical Review Materials, 2021, 5, .	2.4	3
5	Molecular Mechanism and Prevention Strategy of Chemotherapy- and Radiotherapy-Induced Ovarian Damage. International Journal of Molecular Sciences, 2021, 22, 7484.	4.1	34
6	Spinâ€“orbit torque switching in a single (Ga,Mn)(As,P) layer with perpendicular magnetic anisotropy. APL Materials, 2021, 9, .	5.1	6
7	Temperature-induced antiferromagnetic interlayer exchange coupling in (Ga,Mn)(As,P)-based trilayer structure. Journal of Applied Physics, 2020, 127, 183902.	2.5	5
8	Magnetic properties and electronic origin of the interface between dilute magnetic semiconductors with orthogonal magnetic anisotropy. Physical Review Materials, 2020, 4, .	2.4	7
9	Comparing efficacy of high-dose rate brachytherapy versus helical tomotherapy in the treatment of cervical cancer. Journal of Gynecologic Oncology, 2020, 31, e42.	2.2	4
10	Interlayer exchange coupling in (Ga,Mn)As ferromagnetic semiconductor multilayer systems. Journal of Semiconductors, 2019, 40, 081503.	3.7	2
11	Exchange bias in ferromagnetic bilayers with orthogonal anisotropies: the case of GaMnAsP/GaMnAs combination. Scientific Reports, 2019, 9, 13061.	3.3	6
12	Effects of film thickness and annealing on the magnetic properties of GaMnAsP ferromagnetic semiconductor. Journal of Crystal Growth, 2019, 512, 112-118.	1.5	6
13	Noncollinear magnetoresistance of trilayers consisting of two ferromagnetic GaMnAs layers and a nonmagnetic GaAs:Be spacer. Journal of Crystal Growth, 2019, 512, 176-180.	1.5	0
14	Interlayer exchange coupling in ferromagnetic semiconductor trilayers with out-of-plane magnetic anisotropy. Scientific Reports, 2019, 9, 4740.	3.3	4
15	Interlayer Exchange Coupling Between Fe and GaMnAs Ferromagnetic Semiconductor. IEEE Transactions on Magnetics, 2019, 55, 1-4.	2.1	0
16	Spinâ€“Orbit-Induced Effective Magnetic Field in GaMnAs Ferromagnetic Semiconductor. IEEE Transactions on Magnetics, 2019, 55, 1-6.	2.1	3
17	Programmable bias field observed in graded ferromagnetic semiconductor films with broken symmetry. Physical Review Materials, 2019, 3, .	2.4	4
18	Effects on Magnetic Properties of GaMnAs Induced by Proximity of Topological Insulator Bi2Se3. Journal of Electronic Materials, 2018, 47, 4308-4313.	2.2	2

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19	Magnetization reversal in trilayer structures consisting of GaMnAs layers with opposite signs of anisotropic magnetoresistance. Scientific Reports, 2018, 8, 2288.	3.3	2
20	Ferromagnetic resonance and spin-wave resonances in GaMnAsP films. AIP Advances, 2018, 8, 056402.	1.3	4
21	Dependence of ferromagnetic properties on phosphorus concentration in Ga1-xMnxAs1-yPy. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 02D104.	1.2	7
22	In situ annealing of III1-xMnxV ferromagnetic semiconductors. Journal of Vacuum Science and Technology B:Nanotechnology and Microelectronics, 2018, 36, 02D102.	1.2	1
23	Orthogonal interfacial exchange coupling in GaMnAsP/GaMnAs bilayers. AIP Advances, 2018, 8, 056401.	1.3	4
24	Magnetization reversal and interlayer exchange coupling in ferromagnetic metal/semiconductor Fe/GaMnAs hybrid bilayers. Scientific Reports, 2018, 8, 10570.	3.3	5
25	Ovarian tissue cryopreservation and transplantation in patients with cancer. Obstetrics and Gynecology Science, 2018, 61, 431.	1.6	64
26	Magnetic anisotropy of quaternary GaMnAsP ferromagnetic semiconductor. AIP Advances, 2017, 7, .	1.3	13
27	Spacer-thickness dependence of interlayer exchange coupling in GaMnAs/InGaAs/GaMnAs trilayers grown on ZnCdSe buffers. Solid State Communications, 2017, 253, 37-41.	1.9	4
28	Magnetic properties of Ni films deposited on MBE grown Bi2Se3 layers. AIP Advances, 2017, 7, 055819.	1.3	7
29	Interlayer exchange coupling in MBE-grown GaMnAs-based multilayer systems. Journal of Crystal Growth, 2017, 477, 188-192.	1.5	13
30	Manipulation of magnetization in GaMnAs films by spin-orbit-induced magnetic fields. Current Applied Physics, 2017, 17, 801-805.	2.4	7
31	Surface pinning effect of an antiferromagnetic interlayer exchange coupling in (Ga1â^'x Mn x) Tj ETQq1 1 0.784314 rgBT /Overlock 10 T	0.7	0
32	Field-free manipulation of magnetization alignments in a Fe/GaAs/GaMnAs multilayer by spin-orbit-induced magnetic fields. Scientific Reports, 2017, 7, 10162.	3.3	9
33	Non-volatile logic gates based on planar Hall effect in magnetic films with two in-plane easy axes. Scientific Reports, 2017, 7, 1115.	3.3	4
34	Determination of current-induced spin-orbit effective magnetic field in GaMnAs ferromagnetic semiconductor. Applied Physics Letters, 2017, 111, 252401.	3.3	6
35	Effect of Underlying Bi2Se3Surface on Magnetic Properties of Ni Films. IEEE Transactions on Magnetics, 2017, 53, 1-4.	2.1	1
36	Temperature-induced transition of magnetic anisotropy between in-plane and out-of-plane directions in GaMnAs film. Solid State Communications, 2016, 244, 7-11.	1.9	3

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37	Magnetic anisotropy of crystalline Fe films grown on (001) GaAs substrates using Ge buffer layers. AIP Advances, 2016, 6, 055806.	1.3	1
38	Angular Dependence of Tunneling Magnetoresistance in Hybrid Fe/GaAlAs/GaMnAs Magnetic Tunnel Junctions. IEEE Transactions on Magnetics, 2016, 52, 1-4.	2.1	2
39	Experimental determination of next-nearest-neighbor interlayer exchange coupling in ferromagnetic GaMnAs/GaAs:Be multilayers. Applied Physics Letters, 2015, 107, 192403.	3.3	2
40	Observation of uniaxial anisotropy along the [100] direction in crystalline Fe film. Scientific Reports, 2015, 5, 17761.	3.3	10
41	Focusing surface plasmon polaritons through a disordered nanohole structure. , 2015, , .		0
42	Antiferromagnetic Interlayer Exchange Coupling in Ferromagnetic GaMnAs/GaAs:Be Multilayers. IEEE Transactions on Magnetics, 2015, 51, 1-4.	2.1	4
43	Thickness dependence of uniaxial anisotropy fields in GaMnAs films. Applied Physics Express, 2015, 8, 033201.	2.4	5
44	Determination of interlayer exchange fields acting on individual (Ga,Mn)As layers in (Ga,Mn)As/GaAs multilayers. Japanese Journal of Applied Physics, 2015, 54, 033001.	1.5	4
45	Magnetotransport properties of Fe/GaAlAs/GaMnAs hybrid magnetic trilayer structures. Journal of Applied Physics, 2014, 115, 17C715.	2.5	5
46	Decimal Tunneling Magnetoresistance States in Fe/GaAlAs/GaMnAs Magnetic Tunnel Junction. IEEE Transactions on Magnetics, 2014, 50, 1-4.	2.1	2
47	Effect of light illumination on the [100] uniaxial magnetic anisotropy of GaMnAs film. Solid State Communications, 2014, 192, 27-30.	1.9	3
48	Effect of annealing on the magnetic anisotropy of GaMnAs film with low Mn concentration. Current Applied Physics, 2014, 14, S34-S38.	2.4	1
49	Effect of thermal annealing on the magnetic anisotropy of GaMnAs ferromagnetic semiconductor. Current Applied Physics, 2014, 14, 1775-1778.	2.4	6
50	Investigation of the magnetic anisotropy in ferromagnetic GaMnAs films by using the planar hall effect. Journal of the Korean Physical Society, 2013, 62, 2099-2103.	0.7	3
51	Low field magnetization reversal behavior in GaMnAs films. Journal of the Korean Physical Society, 2013, 62, 1473-1478.	0.7	0
52	Temperature Behavior of Uniaxial Anisotropy along [100] Direction in GaMnAs Films. Applied Physics Express, 2013, 6, 013001.	2.4	11
53	Planar Hall effect in a single GaMnAs film grown on Si substrate. Journal of Crystal Growth, 2013, 378, 361-364.	1.5	3
54	Coexistence of magnetic domains with in-plane and out-of-plane anisotropy in a single GaMnAs film. Journal of Crystal Growth, 2013, 378, 337-341.	1.5	2

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55	Quantitative investigation of magnetic domains with in-plane and out-of-plane easy axes in GaMnAs films by Hall effect. Journal of Applied Physics, 2013, 113, .	2.5	4
56	Tunneling magnetoresistance from non-collinear alignment of magnetization in Fe/GaAlAs/GaMnAs magnetic tunnel junctions. Applied Physics Letters, 2013, 102, 212404.	3.3	14
57	The critical role of next-nearest-neighbor interlayer interaction in the magnetic behavior of magnetic/non-magnetic multilayers. New Journal of Physics, 2013, 15, 123025.	2.9	8
58	Quaternary memory device fabricated from a single layer Fe film. Journal of Applied Physics, 2012, 111, 07C704.	2.5	3
59	Field-controllable exchange bias in epitaxial Fe films grown on GaAs. Applied Physics Letters, 2012, 101, 132403.	3.3	5
60	Magnetotransport properties of ferromagnetic semiconductor GaMnAs-based superlattices. Current Applied Physics, 2012, 12, S31-S36.	2.4	5
61	Investigation of superlattices based on ferromagnetic semiconductor GaMnAs by planar Hall effect. Journal of Applied Physics, 2012, 111, 07D310.	2.5	4
62	Crossover critical behavior of Ga<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mrow><mml:mn>1</mml:mn><mml:mo>âˆ’</mml:mo><mml:mi>x</mml:mi></mml:mrow></mml:msub></mml:math>Mn<mml xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mrow /><mml:mi>x</mml:mi></mml:msub></mml:math>As. Physical Review B, 2012, 85, .	3.2	5
63	Use of the Asymmetric Planar Hall Resistance of an Fe Film for Possible Multi-Value Memory Device Applications. Journal of Nanoscience and Nanotechnology, 2011, 11, 5990-5994.	0.9	6
64	Antiferromagnetic exchange coupling between GaMnAs layers separated by a nonmagnetic GaAs:Be spacer. Journal of Applied Physics, 2011, 109, 07C307.	2.5	8
65	Asymmetry in the angular dependence of the switching field of GaMnAs film. Journal of Applied Physics, 2011, 109, 07C308.	2.5	14
66	Power and temperature dependent magneto-photoluminescence of the asymmetric double layers of quantumdots. Journal of Crystal Growth, 2011, 323, 172-175.	1.5	0
67	Magnetic Anisotropy of GaMnAs Film and Its Application in Multi-valued Memory Devices. Japanese Journal of Applied Physics, 2011, 50, 04DM02.	1.5	2
68	Investigation of weak interlayer exchange coupling in GaMnAs/GaAs superlattices with insulating nonmagnetic spacers. Journal of Applied Physics, 2011, 110, .	2.5	15
69	Effect of pinning-field distribution on the process of magnetization reversal in Ga1âˆ’xMnxAs films. Physical Review B, 2011, 84, .	3.2	11
70	Magnetic Anisotropy of GaMnAs Film and Its Application in Multi-valued Memory Devices. Japanese Journal of Applied Physics, 2011, 50, 04DM02.	1.5	2
71	Mapping of magnetic anisotropy in strained ferromagnetic semiconductor GaMnAs films. Journal of Applied Physics, 2010, 107, .	2.5	21
72	Investigation of domain pinning fields in ferromagnetic GaMnAs films using angular dependence of the planar Hall effect. Solid State Communications, 2010, 150, 27-29.	1.9	14

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73	Influence of uniaxial anisotropy on the domain pinning fields of ferromagnetic Ga1â^'xMnxAs films. Journal of Applied Physics, 2010, 108, 063910.	2.5	8
74	Carrier transfer from wetting layer to quantum dots studied by cw-resolved and time-resolved photoluminescence in CdSe/ZnSe quantum dot system. Journal of Applied Physics, 2010, 107, 063517.	2.5	1
75	Magnetization reorientation inGaxMn1â^'xAsfilms: Planar Hall effect measurements. Physical Review B, 2010, 81, .	3.2	11
76	Observation of antiferromagnetic interlayer exchange coupling in a<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:mrow><mml:msub><mml:mrow><mml:mtext>Ga</mml:mtext></mml:mrow><mml:mrow><mml:mn>1</mml:m Physical Review B, 2010, 82, .	3.2	27
77	Vertical gradient of magnetic anisotropy in the ferromagnetic semiconductor (Ga,Mn)As film. Applied Physics Letters, 2010, 96, 092105.	3.3	6
78	Giant magnetoresistance and long-range antiferromagnetic interlayer exchange coupling in (Ga,Mn)As/GaAs:Be multilayers. Physical Review B, 2010, 82, .	3.2	33
79	Asymmetry in the planar Hall resistance of Fe films grown on vicinal GaAs substrates. Journal of Applied Physics, 2010, 107, 09C505.	2.5	8
80	Magnetic anisotropy of Ga1â^'xMnxAs films with additional nonmagnetic donor doping. Journal of Applied Physics, 2010, 107, 09C303.	2.5	3
81	Asymmetry in the reorientation process of magnetization for crossing the [11Â¯0] and the [110] directions in Ga1â^'xMnxAs epilayers. Journal of Applied Physics, 2010, 107, 09C304.	2.5	1
82	Reduction in the planar Hall resistance amplitude in the reversal process of Fe film with biaxial easy axes. Journal of Applied Physics, 2010, 107, 09C508.	2.5	2
83	Four discrete Hall resistance states in single-layer Fe film for quaternary memory devices. Applied Physics Letters, 2009, 95, 202505.	3.3	16
84	Magnetotransport properties of GaMnAs based trilayer structures with different thicknesses of InGaAs spacer layer. Journal of Applied Physics, 2009, 105, 07C505.	2.5	8
85	Quantitative analysis of the angle dependence of planar Hall effect observed in ferromagnetic GaMnAs film. Journal of Applied Physics, 2009, 105, .	2.5	12
86	Four Stable Magnetization States Formed in the Single Layer of GaMnAs Ferromagnetic Film. Materials Research Society Symposia Proceedings, 2009, 1183, 31.	0.1	0
87	Ferromagnetic semiconductor GaMnAs. Materials Today, 2009, 12, 14-21.	14.2	52
88	Temperature dependence of magnetization in GaMnAs film with critical strain. Solid State Communications, 2009, 149, 1300-1303.	1.9	6
89	The effect of carrier density on magnetic anisotropy of the ferromagnetic semiconductor (Ga, Mn)As. Solid State Communications, 2009, 149, 1739-1742.	1.9	17
90	Monitoring of magnetization processes in GaMnAs ferromagnetic film by electrical transport measurement. Journal of Crystal Growth, 2009, 311, 925-928.	1.5	2

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91	Magneto-transport Properties of a GaMnAs-Based Ferromagnetic Semiconductor Trilayer Structure Grown on a ZnMnSe Buffer. Journal of Electronic Materials, 2008, 37, 912-916.	2.2	6
92	Effect of chemical etching on magnetic anisotropy of ferromagnetic GaMnAs films studied by planar Hall effect. Solid State Communications, 2008, 147, 309-312.	1.9	5
93	Quantitative investigation of the magnetic anisotropy in GaMnAs film by using Hall measurement. Journal of Applied Physics, 2008, 103, .	2.5	51
94	Distribution of magnetic domain pinning fields inGa1â^’xMnxAsferromagnetic films. Physical Review B, 2008, 78, .	3.2	21
95	Carrier-Mediated Antiferromagnetic Interlayer Exchange Coupling in Diluted Magnetic Semiconductor Multilayers<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>Ga</mml:mi><mml:mrow><mml:mn>1</mml:mn><mml:mo>â^’</mml:mo><mml:mi>x</mml:mi mathvariant="normal">:</mml:mtext><mml:mi>Be</mml:mi></mml:math>. Physical Review Letters, 2008, 101, 237202.	7.8	54
96	Single and multidomain characteristics of GaMnAs investigated by magnetotransport measurements. Journal of Applied Physics, 2008, 103, .	2.5	14
97	Influence of Resonant Excitation and Carrier Lifetime on the Optical Properties of Coupled CdSe Quantum Dots. Journal of the Korean Physical Society, 2008, 53, 106-109.	0.7	3
98	Tunable quaternary states in ferromagnetic semiconductor GaMnAs single layer for memory devices. Applied Physics Letters, 2007, 90, 152113.	3.3	17
99	Stable Multidomain Structures Formed in the Process of Magnetization Reversal in GaMnAs Ferromagnetic Semiconductor Thin Films. Physical Review Letters, 2007, 98, 047201.	7.8	63
100	Temperature dependence of magnetic anisotropy in ferromagnetic (Ga,Mn)As films: Investigation by the planar Hall effect. Physical Review B, 2007, 76, .	3.2	61
101	Localization and interdot carrier transfer in CdSe and CdZnMnSe quantum dots determined by cw and time-resolved photoluminescence. Applied Physics Letters, 2007, 90, 201916.	3.3	12
102	Zeeman mapping of exciton localization in self-assembled CdSe quantum dots using diluted magnetic semiconductors. Solid State Communications, 2007, 141, 311-315.	1.9	6
103	Time stability of multi-domain states formed in the magnetization reversal process of GaMnAs film. Solid State Communications, 2007, 143, 232-235.	1.9	12
104	Growth and magneto-optical properties of CdSe/ZnMnSe self-assembled quantum dots. Journal of Crystal Growth, 2007, 301-302, 781-784.	1.5	1
105	Enhancement of magnetic field in superconductor and magnetic semiconductor quantum well hybrid structure. Journal of Crystal Growth, 2007, 301-302, 906-909.	1.5	2
106	Magneto-Optical Properties of Non-Magnetic Semiconductor Quantum dot and Magnetic Quantum well Coupled Structures. Journal of the Korean Physical Society, 2007, 50, 824.	0.7	1
107	Strain-Engineered Magnetic Anisotropy of GaMnAs Ferromagnetic Semiconductors. Journal of the Korean Physical Society, 2007, 50, 829.	0.7	1
108	Inter-dot spin exchange interaction in coupled IIâ€“VI semiconductor quantum dots. Physica Status Solidi (B): Basic Research, 2006, 243, 799-804.	1.5	4

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109	Four states memory function in GaMnAs ferromagenic semiconductor epilayer. , 2006, , .		0
110	Coupling-dependent spin polarization of quantum dots in double layer geometry. Journal of Crystal Growth, 2005, 275, e2295-e2300.	1.5	1
111	Effect of Low Temperature Annealing on the Magnetic Properties of Ga1?xMnxAs/GaAs Superlattices. Journal of Superconductivity and Novel Magnetism, 2005, 18, 93-96.	0.5	1
112	Effect of Interlayer Exchange Coupling on the Curie Temperature in Ga1-xMnxAs Trilayer Structures. Japanese Journal of Applied Physics, 2004, 43, 2093-2096.	1.5	2
113	Magneto-photoluminescence study on magnetic/non-magnetic semiconductor coupled quantum dots. Physica Status Solidi (B): Basic Research, 2004, 241, 722-726.	1.5	1
114	Polarization selective magneto-optical study on the coupled quantum dots using resonant excitation. Physica E: Low-Dimensional Systems and Nanostructures, 2004, 21, 376-380.	2.7	1
115	Title is missing!. Journal of Superconductivity and Novel Magnetism, 2003, 16, 453-456.	0.5	5
116	Effect of additional nonmagnetic acceptor doping on the resistivity peak and the Curie temperature of Ga1â^'xMnxAs epitaxial layers. Applied Physics Letters, 2003, 82, 1206-1208.	3.3	53
117	Variation of Inter-Well Coupling in Magnetically Tunable Multiple Quantum Wells. Physica Status Solidi (B): Basic Research, 2002, 229, 711-716.	1.5	2